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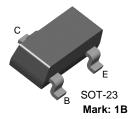
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### **MMBT2222**

### **NPN General Purpose Amplifier**

• Sourced from process 19.



### **Absolute Maximum Ratings\*** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	0.6	Α
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

<sup>\*</sup> This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These rating are based on a maximum junction temperature of 150 degrees C.
These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Electrical Characteristics** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	30		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10\mu A, I_{E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		10	μΑ
		$V_{CB} = 50V, I_{E} = 0, T_{a} = 125^{\circ}C$		10	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$		10	nA
On Charac	cteristics				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1mA, V <sub>CE</sub> = 10V	35		
		$I_C = 1.0 \text{mA}, V_{CE} = 10 \text{V}$	50		
		$I_C = 10 \text{mA}, V_{CE} = 10 \text{V}$	75		
		$I_C = 150 \text{mA}, V_{CE} = 10 \text{V}^*$	100	300	
		$I_C = 150 \text{mA}, V_{CF} = 1.0 \text{V}^*$	50		
		I <sub>C</sub> = 500mA, V <sub>CE</sub> = 10V *	30		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		0.4	V
- (32-7)		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		1.6	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		1.3	V
. ,		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		2.6	

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# $\textbf{Electrical Characteristics} \hspace{0.1cm} \text{(Continued)} \hspace{0.2cm} \textbf{T}_{a} = 25^{\circ} \textbf{C} \hspace{0.1cm} \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Max.	Units
Small Sign	nal Characteristics	·			
f <sub>T</sub>	Curent Gain Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 20V, f = 100MHz	250		
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		8.0	pF
C <sub>ibo</sub>	Input Capacitance	$V_{EB} = 0.5V, I_{C} = 0, f = 1MHz$		30	pF
Switching	Characteristics	·			
t <sub>d</sub>	Delay Time	$V_{CC} = 30V, V_{BE(OFF)} = 0.5V,$		10	ns
t <sub>r</sub>	Rise Time	I <sub>C</sub> = 150mA, I <sub>B1</sub> = 15mA		25	ns
t <sub>s</sub>	Storage Time	$V_{CC} = 30V, I_{C} = 150mA,$		225	ns
t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 15mA$		60	ns

<sup>\*</sup> Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

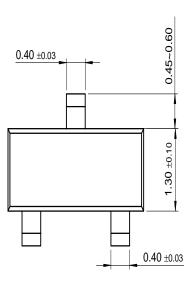
## Thermal Characteristics $\rm T_a=25^{\circ}C$ unless otherwise noted

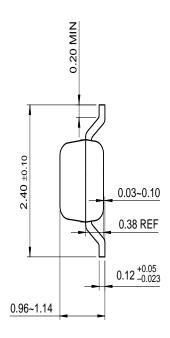
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

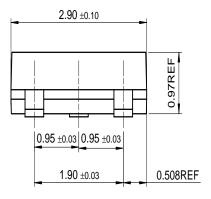
<sup>\*</sup> Device mounted on FR-4PCB 1.6" × 1.6" × 0.06".

# **Package Dimensions**

# SOT-23







Dimensions in Millimeters

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### **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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